

IN THE CLAIMS

Please amend the claims as follows:

1.-29. (Canceled)

30. (New) A thin-film transistor comprising:

a source region and a drain region which are provided with an interval on an insulating substrate;

a gate insulator layer which is provided over the interval between the source region and the drain region;

a gate electrode which is provided on the gate insulator layer; and

a source electrode and a drain electrode which are provided on the source region and the drain region, respectively, wherein

the gate electrode comprises:

a first metal diffusion-preventing layer formed on the gate insulator layer;

a metal seed layer formed on the first metal diffusion-preventing layer;

a metal layer formed on the metal seed layer; and

a second metal diffusion-preventing layer covering the exposed surface including the side surface of the multilayered structure having the metal seed layer and the metal layer, and wherein

the metal seed layer and the metal layer are surrounded by the first metal diffusion-preventing layer and the second metal diffusion-preventing layer, and have a forward tapered cross section.

31. (New) The thin-film transistor according to claim 30, wherein the source electrode and the drain electrode comprises:

a third metal diffusion-preventing layer formed on the source region and the drain region;

a copper wiring layer formed on the third metal diffusion-preventing layer; and

a fourth metal diffusion-preventing layer formed to surround the copper wiring layer.

32. (New) The thin-film transistor according to claim 31, wherein the gate electrode, the source electrode, and the drain electrode each has wiring connected thereto, and the wiring comprises:

a fifth metal diffusion-preventing layer which is provided on one of the substrate and the insulator layer;

a metal seed layer formed on the fifth metal diffusion-preventing layer;

a metal wiring layer of forward tapered cross section which is provided on the metal seed layer and connects one end thereof to any one of the gate electrode, the source electrode, and the drain electrode; and

a sixth metal diffusion-preventing layer covering the exposed surface including the side surface of the multilayered structure having the metal seed layer and the metal wiring layer, and wherein

the metal seed layer and the metal wiring layer are surrounded by the first metal diffusion-preventing layer and the second metal diffusion-preventing layer.

33. (New) The thin-film transistor according to claim 32, wherein a plurality of the thin-film transistors are arranged to form a matrix, and the thin-film transistors have scanning

lines connected to the gate electrodes of the thin-film transistors, and signal lines connected to one of the source electrodes and the drain electrodes of the thin-film transistors, the signal lines being provided such that they are surrounded by the first metal diffusion-preventing layer and the second metal diffusion-preventing layer.

34. (New) The thin-film transistor according to claim 30, wherein the insulating substrate is formed of one of glass, a quartz glass, ceramics, and a resin material.

35. (New) A thin-film transistor comprising:

a source region and a drain region which are provided with an interval on an insulating substrate:

a gate insulator layer which is provided over the interval between the source region and the drain region;

a gate electrode which is provided on the gate insulator layer; and

a source electrode and a drain electrode which are provided on the source region and the drain region, respectively, wherein

the gate electrode comprises:

a first metal diffusion-preventing layer formed on the gate insulator layer;

a metal seed layer formed on the first metal diffusion-preventing layer;

a metal layer formed on the metal seed layer and having a forward tapered cross section; and

a second metal diffusion-preventing layer covering the exposed surface including the side surface of the multilayered structure having the metal seed layer, the metal layer and the first metal diffusion-preventing layer, and wherein

the metal seed layer and the metal layer are surrounded by the first metal diffusion-preventing layer and the second metal diffusion-preventing layer.

36. (New) The thin-film transistor according to claim 35, wherein the insulating substrate is formed of one of glass, a quartz glass, ceramics, and a resin material.

37. (New) A thin-film transistor comprising:

a source region and a drain region which are provided with an interval on an insulating substrate;

a gate insulator layer which is provided over the interval between the source region and the drain region;

a gate electrode which is provided on the gate insulator layer; and

a source electrode and a drain electrode which are provided on the source region and the drain region, respectively, wherein

the gate electrode comprises:

a first metal diffusion-preventing layer formed on the gate insulator layer;

a metal layer formed on the first metal diffusion-preventing layer; and

a second metal diffusion-preventing layer covering the exposed surface including the side surface of the multilayered structure having the metal layer and the first metal diffusion-preventing layer, and wherein

the metal layer is surrounded by the first metal diffusion-preventing layer and the second metal diffusion-preventing layer, and has a forward tapered cross section.

38. (New) The thin-film transistor according to claim 37, wherein the insulating substrate is formed of one of glass, a quartz glass, ceramics, and a resin material.